

# 2SB0779 (2SB779)

## Silicon PNP epitaxial planar type

For low-frequency output amplification

### ■ Features

- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Satisfactory linearity of forward current transfer ratio  $h_{FE}$  at the low collector voltage
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	-25	V
Collector-emitter voltage (Base open)	$V_{CEO}$	-20	V
Emitter-base voltage (Collector open)	$V_{EBO}$	-7	V
Collector current	$I_C$	-500	mA
Peak collector current	$I_{CP}$	-1	A
Collector power dissipation	$P_C$	200	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

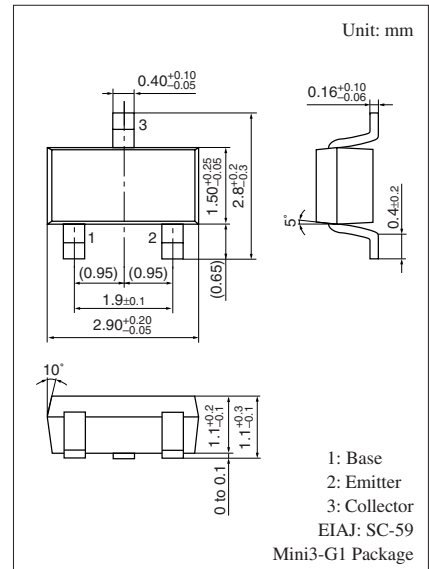
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = -10 \mu\text{A}$ , $I_E = 0$	-25			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = -1 \text{ mA}$ , $I_B = 0$	-20			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = -10 \mu\text{A}$ , $I_C = 0$	-7			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -25 \text{ V}$ , $I_E = 0$			-100	nA
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = -20 \text{ V}$ , $I_B = 0$			-1	$\mu\text{A}$
Forward current transfer ratio *1	$h_{FE1}$ *2	$V_{CE} = -2 \text{ V}$ , $I_C = -500 \text{ mA}$	90		220	—
	$h_{FE2}$	$V_{CE} = -2 \text{ V}$ , $I_C = -1 \text{ A}$	25			—
Collector-emitter saturation voltage *1	$V_{CE(sat)}$	$I_C = -500 \text{ mA}$ , $I_B = -50 \text{ mA}$		-0.2	-0.4	V
Base-emitter saturation voltage *1	$V_{BE(sat)}$	$I_C = -500 \text{ mA}$ , $I_B = -50 \text{ mA}$			-1.2	V
Transition frequency	$f_T$	$V_{CB} = -10 \text{ V}$ , $I_E = 50 \text{ mA}$ , $f = 200 \text{ MHz}$		150		MHz
Collector output capacitance (Common-emitter reverse transfer)	$C_{ob}$	$V_{CB} = -10 \text{ V}$ , $I_E = 0$ , $f = 1 \text{ MHz}$		15		pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*1: Pulse measurement

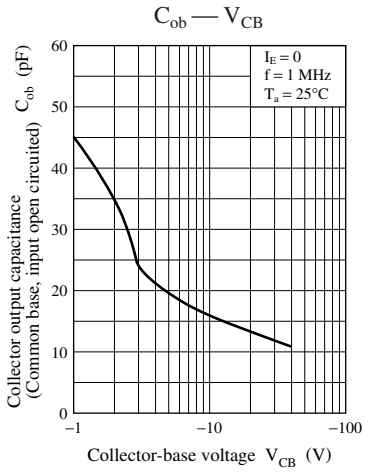
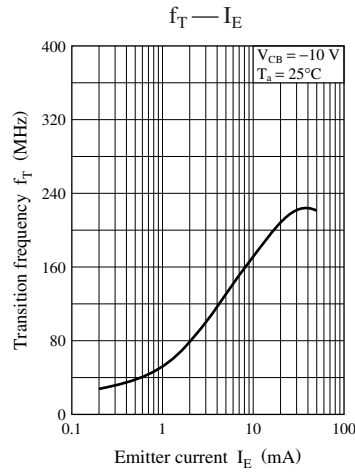
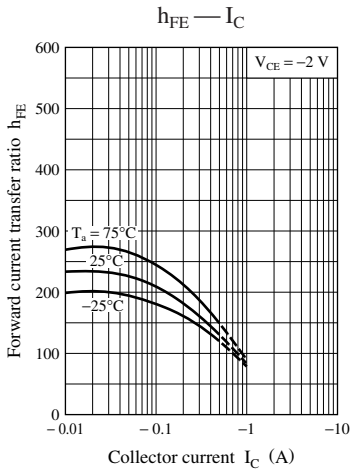
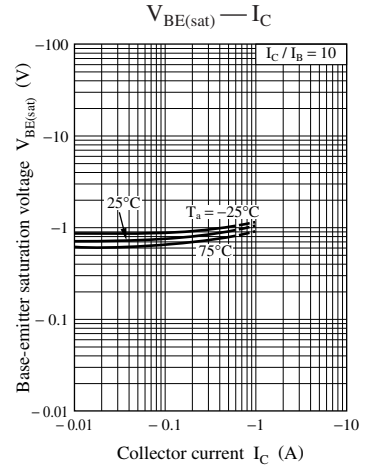
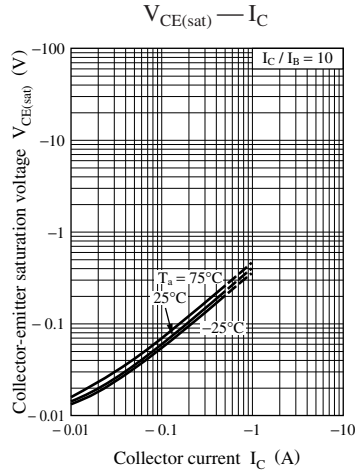
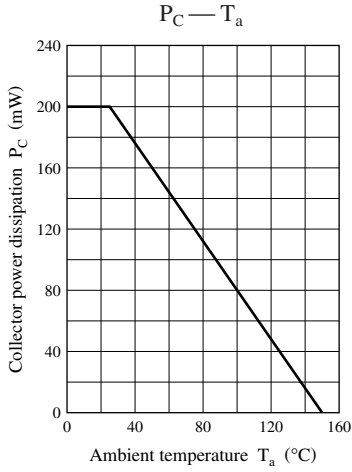
\*2: Rank classification

Rank	Q	R
$h_{FE1}$	90 to 155	130 to 220



Marking Symbol: 1A

Note) The part number in the parenthesis shows conventional part number.



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